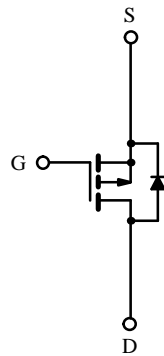
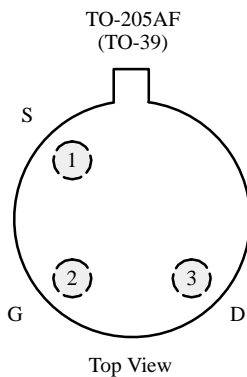


N-Channel Enhancement-Mode Transistor

Product Summary

$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A)
-100	0.30	-6.5

Parametric limits in accordance with MIL-S-19500/564 where applicable.



P-Channel MOSFET

Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$ Unless Otherwise Noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-100	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150^\circ\text{C}$)	I_D	$T_C = 25^\circ\text{C}$	-6.5
		$T_C = 100^\circ\text{C}$	-3.1
Pulsed Drain Current	I_{DM}	-25	A
Avalanche Current	I_{AR}	-3.1	
Maximum Power Dissipation	P_D	$T_C = 25^\circ\text{C}$	25
		$T_C = 100^\circ\text{C}$	10
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$
Lead Temperature ($1/16''$ from case for 10 sec.)	T_L	300	

Thermal Resistance Ratings

Parameter	Symbol	Limit	Unit
Maximum Junction-to-Ambient	R_{thJA}	175	$^\circ\text{C}/\text{W}$
Maximum Junction-to-Case	R_{thJC}	5.0	

Subsequent updates to this data sheet may be obtained via facsimile by calling Siliconix FaxBack, 1-408-970-5600. Please request FaxBack document #1489.

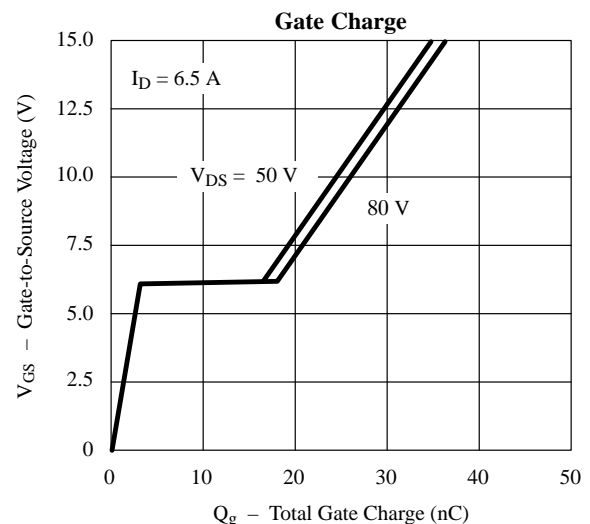
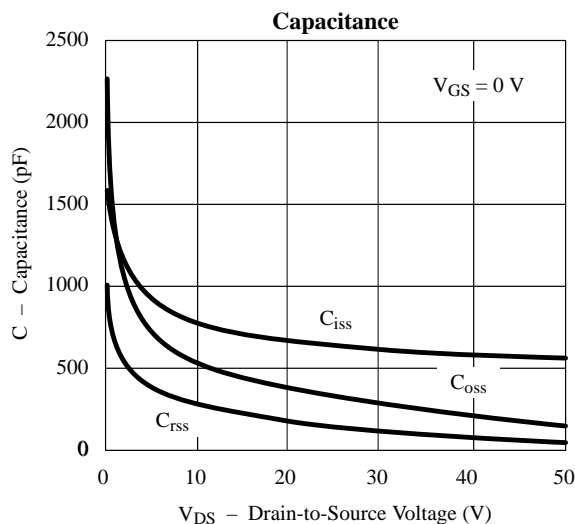
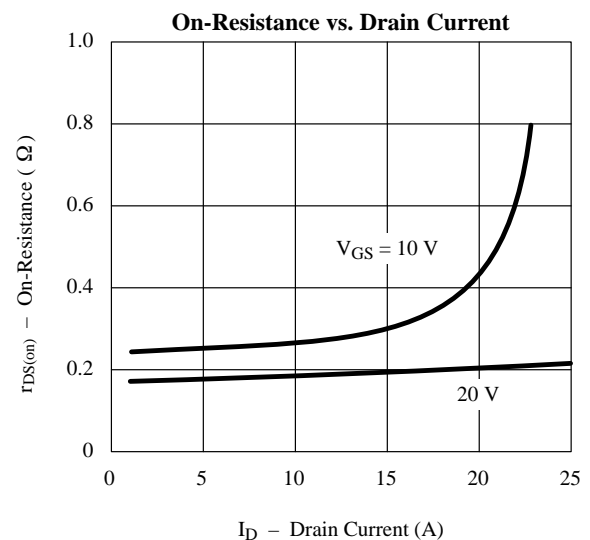
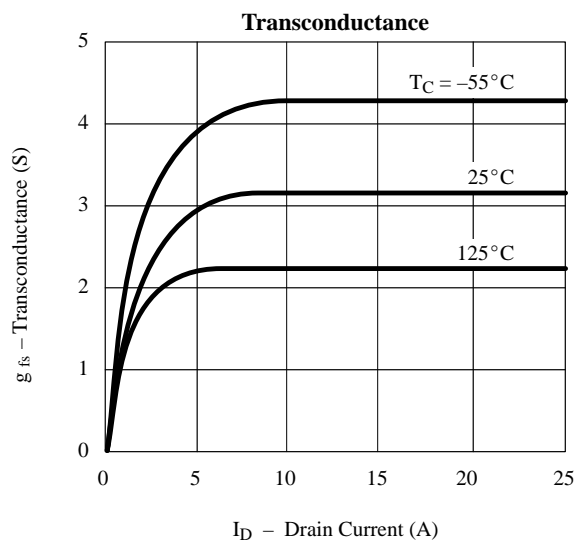
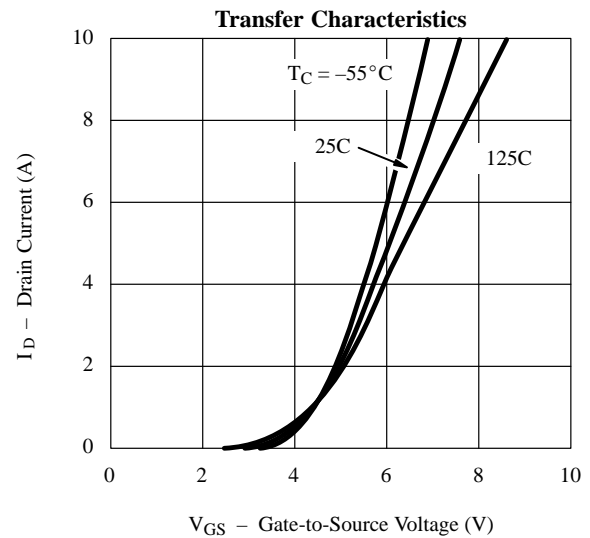
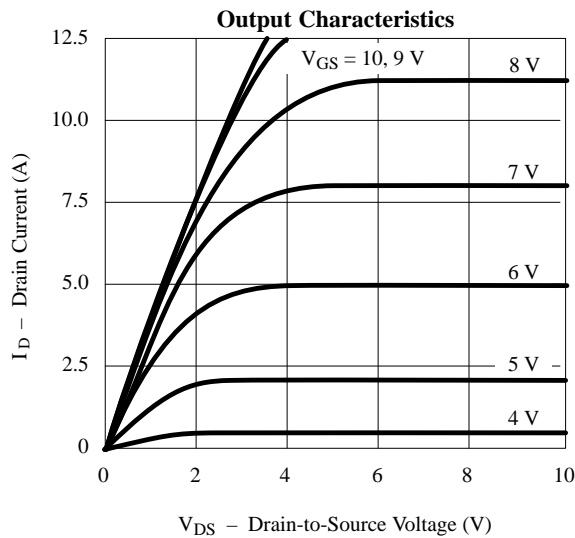
Specifications ($T_J = 25^\circ\text{C}$ Unless Otherwise Noted)

Parameter	Symbol	Test Condition	Limit			Unit
			Min	Typ ^a	Max	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = -1000\ \mu\text{A}$	-100			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-2.0		-4.0	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -80\text{ V}, V_{GS} = 0\text{ V}$			-25	μA
		$V_{DS} = -80\text{ V}, V_{GS} = 0\text{ V}, T_J = 125^\circ\text{C}$			-250	
On-State Drain Current ^b	$I_{D(on)}$	$V_{DS} = -2.1\text{ V}, V_{GS} = -10\text{ V}$	-6.5			A
Drain-Source On-State Resistance ^b	$r_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -4.1\text{ A}$		0.25	0.30	Ω
		$V_{GS} = -10\text{ V}, I_D = -4.1\text{ A}, T_J = 125^\circ\text{C}$		0.40	0.54	
Forward Transconductance ^b	g_{fs}	$V_{DS} = -15\text{ V}, I_D = -4.1\text{ A}$	2.5	2.8	7.5	S
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = -25\text{ V}, f = 1\text{ MHz}$		625		pF
Output Capacitance	C_{oss}			280		
Reverse Transfer Capacitance	C_{rss}			105		
Total Gate Charge ^c	Q_g	$V_{DS} = -50\text{ V}, V_{GS} = -10\text{ V}, I_D = -6.5\text{ A}$	14.7	24	34.8	nC
Gate-Source Charge ^c	Q_{gs}		0.8	3.4	6.8	
Gate-Drain Charge ^c	Q_{gd}		2.0	13.5	23.1	
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = -50\text{ V}, R_L = 10\ \Omega$ $I_D \cong -4.1\text{ A}, V_{GEN} = -10\text{ V}, R_G = 7.5\ \Omega$		9	60	ns
Rise Time ^c	t_r			50	140	
Turn-Off Delay Time ^c	$t_{d(off)}$			32	140	
Fall Time ^c	t_f			38	140	
Source-Drain Diode Ratings and Characteristics						
Continuous Current	I_S				-6.5	A
Pulsed Current	I_{SM}				-25	
Diode Forward Voltage ^b	V_{SD}	$I_F = -6.5\text{ A}, V_{GS} = 0\text{ V}$	-0.8		-2.0	V
Reverse Recovery Time	t_{rr}	$I_F = -6.5\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		110	250	ns
Reverse Recovery Charge	Q_{rr}			0.4		μC

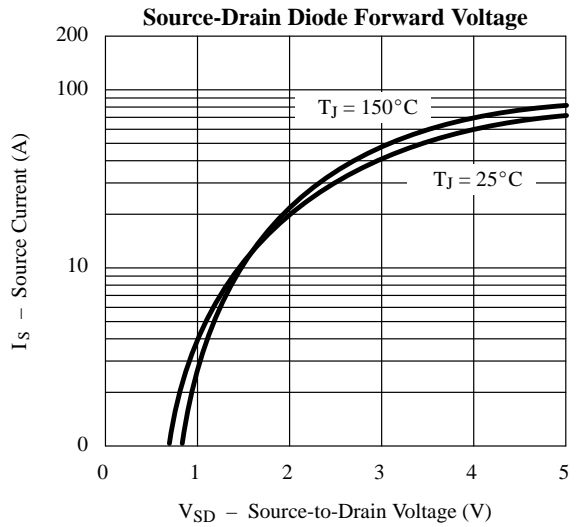
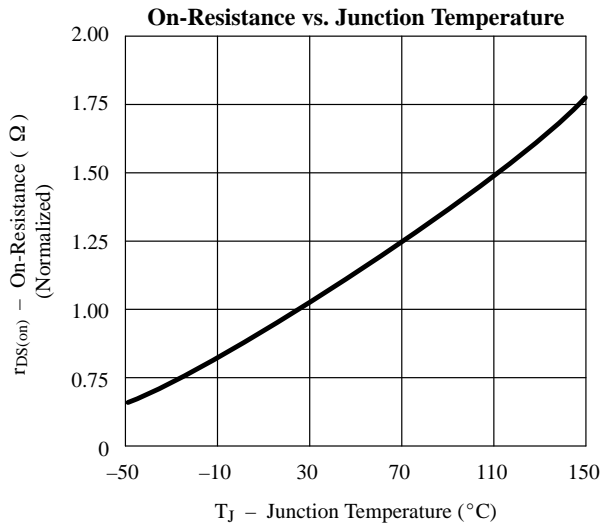
Notes:

- a. For design aid only; not subject to production testing.
 b. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
 c. Independent of operating temperature.

Typical Characteristics (25°C Unless Otherwise Noted)



Typical Characteristics (25°C Unless Otherwise Noted)



Thermal Ratings

